

Vinylidenedithiophenmethylenoxindole: A Centrosymmetric Building block for Donor–Acceptor Copolymers

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Keywords: Field-Effect Transistors, Copolymers, Building blocks, Vinylidenedithiophenmethylenoxindoles, Donor–Acceptor Structure

1. Thermogravimetric analysis (TGA) of VDTOI-based monomer **4** and copolymers.

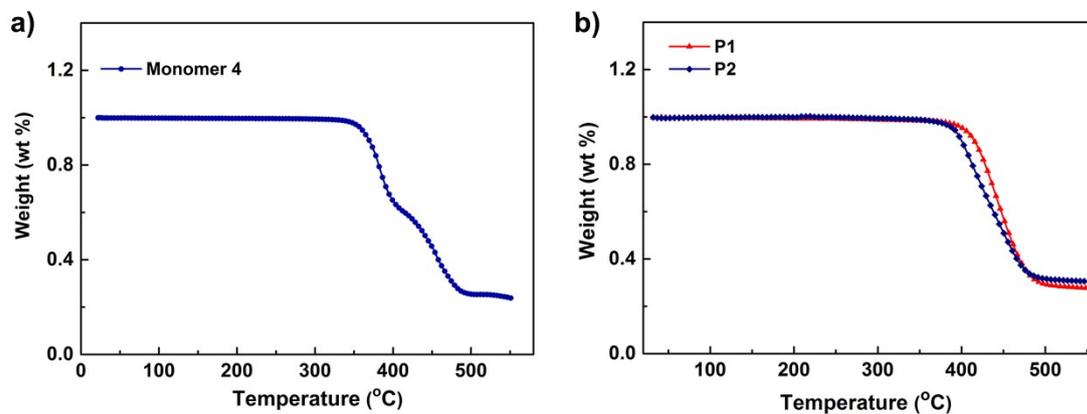


Figure S1. TGA traces of VDTOI-based monomer **4** and copolymers.

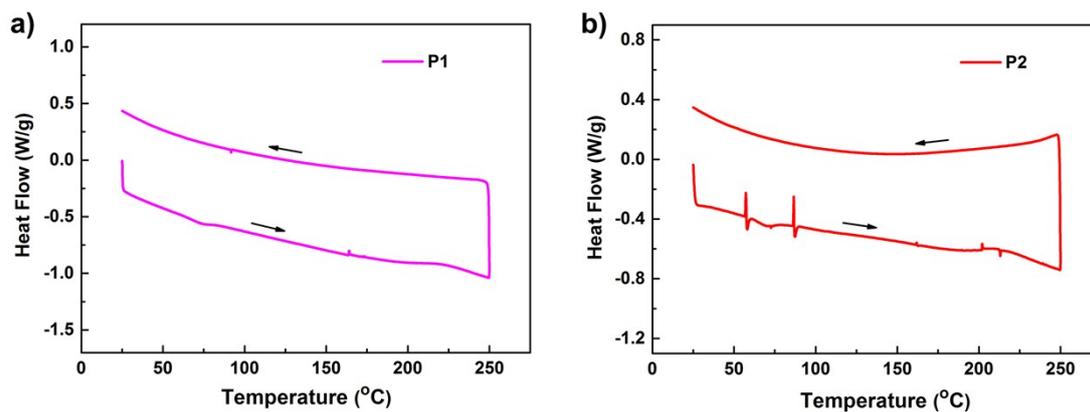


Figure S2. DSC traces of VDTOI-based copolymers. 没有给出单体 **4** 的

2. Electrochemical properties of the VDTOI-based copolymers.

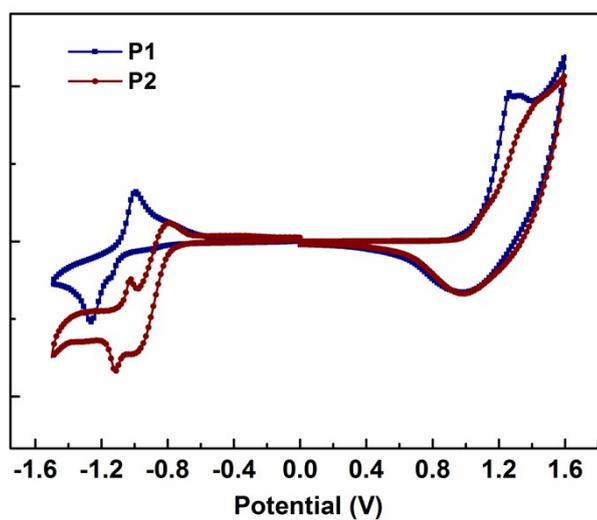


Figure S3. CV traces of the VDTOI-based copolymers.

3. The device performance of the P2-based FETs.

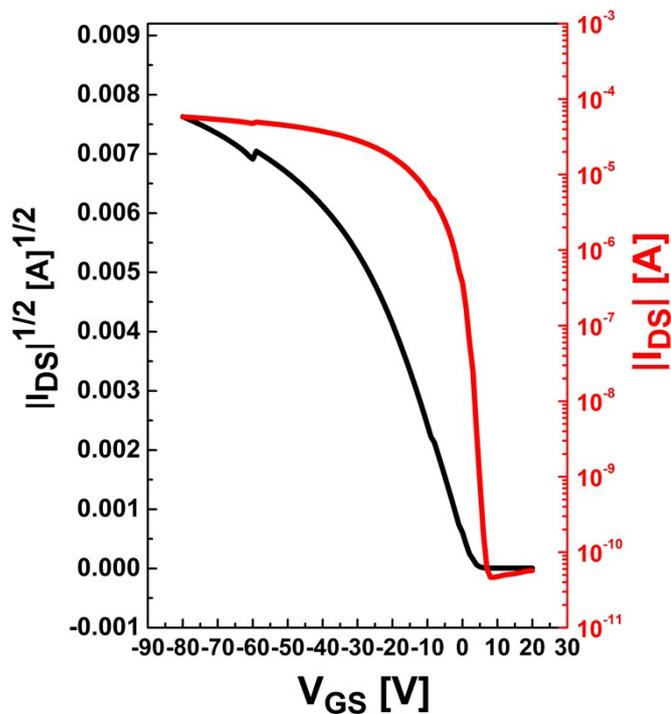


Figure S4. Typical transfer curves of the P2-based FETs.

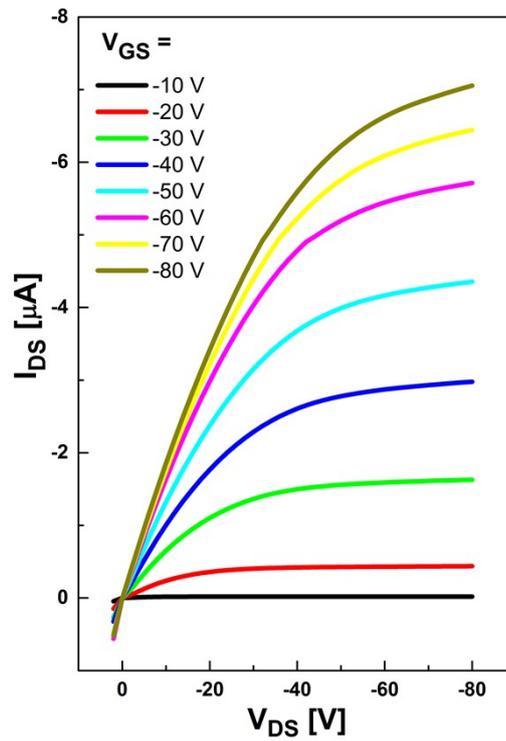


Figure S5. Typical output curves of the **P2**-based FETs.

4. AFM topography images of the **VDTOI**-based copolymers.

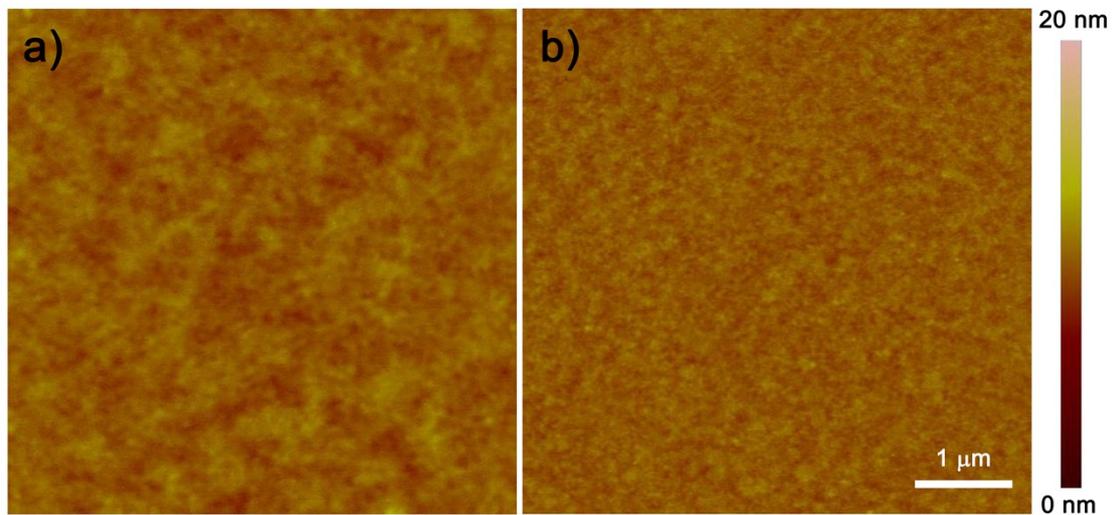


Figure S6. AFM topography images of the **P1** thin films on PTS-modified SiO_2/Si substrates. (a) As-fabricated film and (b) After annealed at $140\text{ }^\circ\text{C}$ for 5 min. All images are $5\text{ }\mu\text{m} \times 5\text{ }\mu\text{m}$ in size.

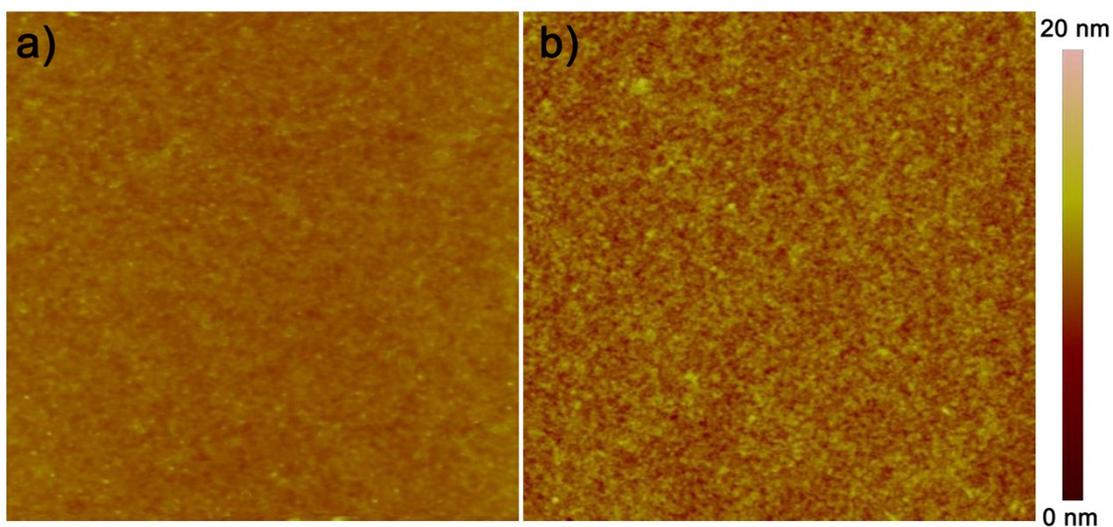


Figure S7. AFM topography images of the **P2** thin films on PTS-modified SiO₂/Si substrates. (a) As-fabricated film and (b) After annealed at 140 °C for 5 min. All images are 5 μm × 5 μm in size.

5. A2D-GXRD pattern of the **P2** thin films,

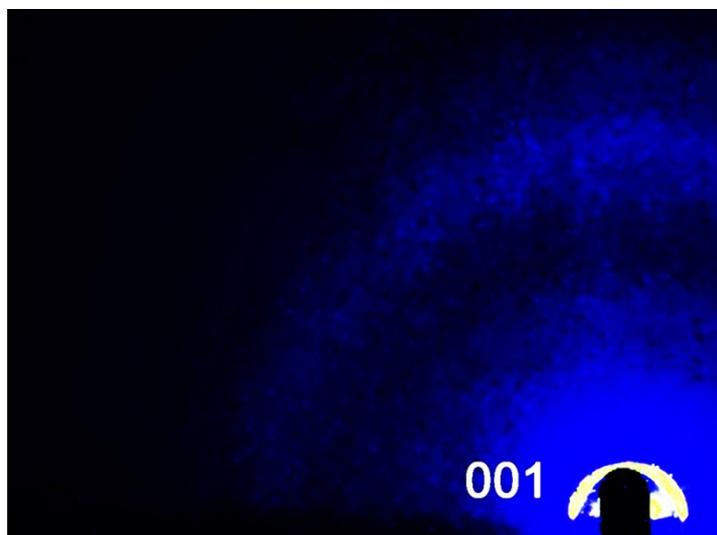


Figure S8. 2D-GXRD pattern of of the **P2** thin films on PTS -modified SiO₂/Si substrates after annealing at 140 °C for 5 min.